

1A Axial High Efficiency Rectifier

PRODUCT SUMMARY

Voltage range 50 to 1000 Volts Popular DO204AL/DO-41 axial package

FEATURES

Plastic package has Underwriters Laboratories Flammability Classification 94V-0

High current capability

Diffused junction

Ultra fast switching for high efficiency

High temperature soldering guaranteed: 350°C for 10 seconds with 0.375" (9.5mm) lead length and 5 lbs. (2.3kg) tension Maximum Tj is 150°C and maximum Tstg is 175°C with PI glue

MECHANICAL DATA

Case: JEDEC DO-204AL (DO-41), molded plastic body

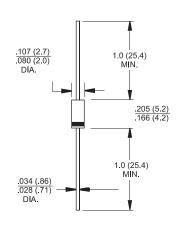
Terminals: Matte-Sn plated axial leads, solderable per MIL-STD-750,

Method 2026

Polarity: Color band denotes cathode end

Mounting position: any Weight: 0.012 ounce, 0.r

DO-204AL/DO-41



Dimensions in inches and (millimeters)

Pb-free, RoHS compliant.

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25°C ambient temperature unless otherwise specified. Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate current by 20%

Parameter	Symbols	HER 1001	HER 1002	HER 1003	HER 1004	HER 1005	HER 1006	HER 1007	Units
Maximum repetitive peak reverse voltage	V _{RRM}	50	100	200	400	600	800	1000	Volts
Maximum RMS voltage	V _{RMS}	35	70	140	280	420	560	700	Volts
Maximum DC blocking voltage	V _{DC}	50	100	200	400	600	800	1000	Volts
Maximum average forward rectified current @T _A =55°C	I _{F(AV)}	1.0							Amp
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	30.0							Amps
Maximum forward voltage at 1.0A DC	V _F	1.0 1.3 1.7					1.7		Volts
Maximum DC reverse current @ T _J =25°C at rated DC blocking voltage @ T _J =100°C	l _R	5.0 100							uA uA
Maximum reverse recovery time (Note 1)	t _{rr}	50 100					nS		
Typical junction capacitance (Note 2)	C _J	20 10						pF	
Typical thermal resistance (Note 3)	R _{eJA}	25							°C/W
Operating junction temperature range	T _J	-55 to +125							°C
Storage temperature range	T _{STG}	-55 to +150							°C

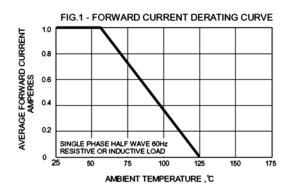
Notes: 1. Measured with I_E=0.5A,I_B=1A,I_{BB}=0.25A.

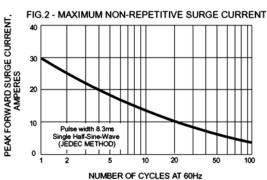
2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

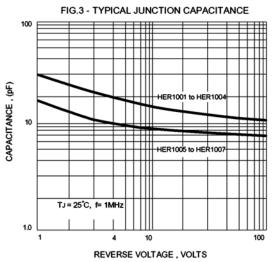
3. Thermal Resistance Junction to Ambient.

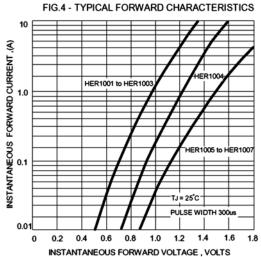


RATINGS AND CHARACTERISTIC CURVES (TA = 25°C unless otherwise noted)









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